

BD912

Rev. H Oct.-2018

TO-220

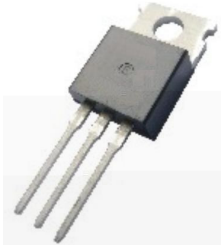
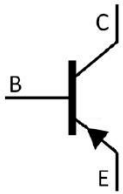
PNP

Silicon PNP transistor in a TO-220 Plastic Package.

, BD911

High V_{CE0} , high I_C , complement to BD911.

Use in power linear and switching applications.



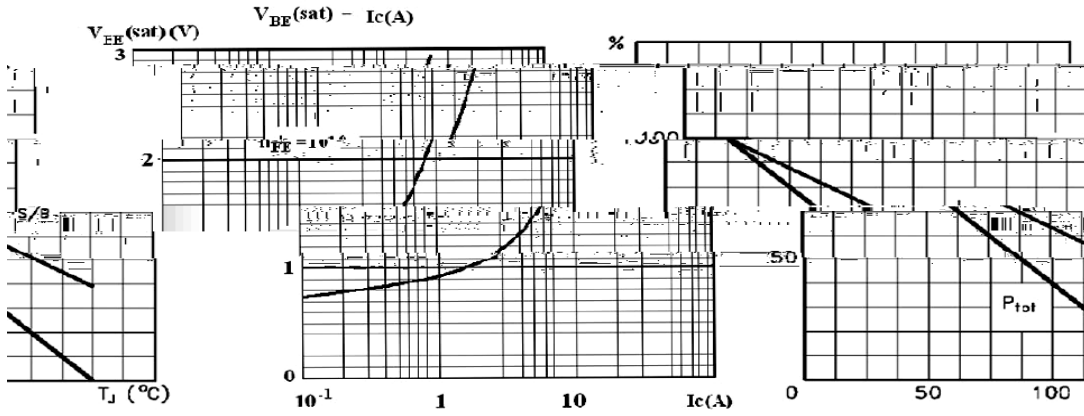
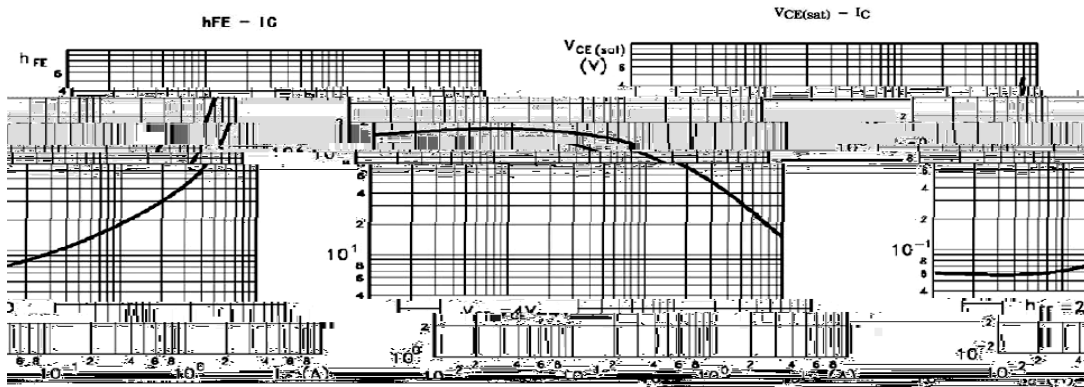
PIN1	Base	PIN 2	Collector	PIN 3	Emitter
440					

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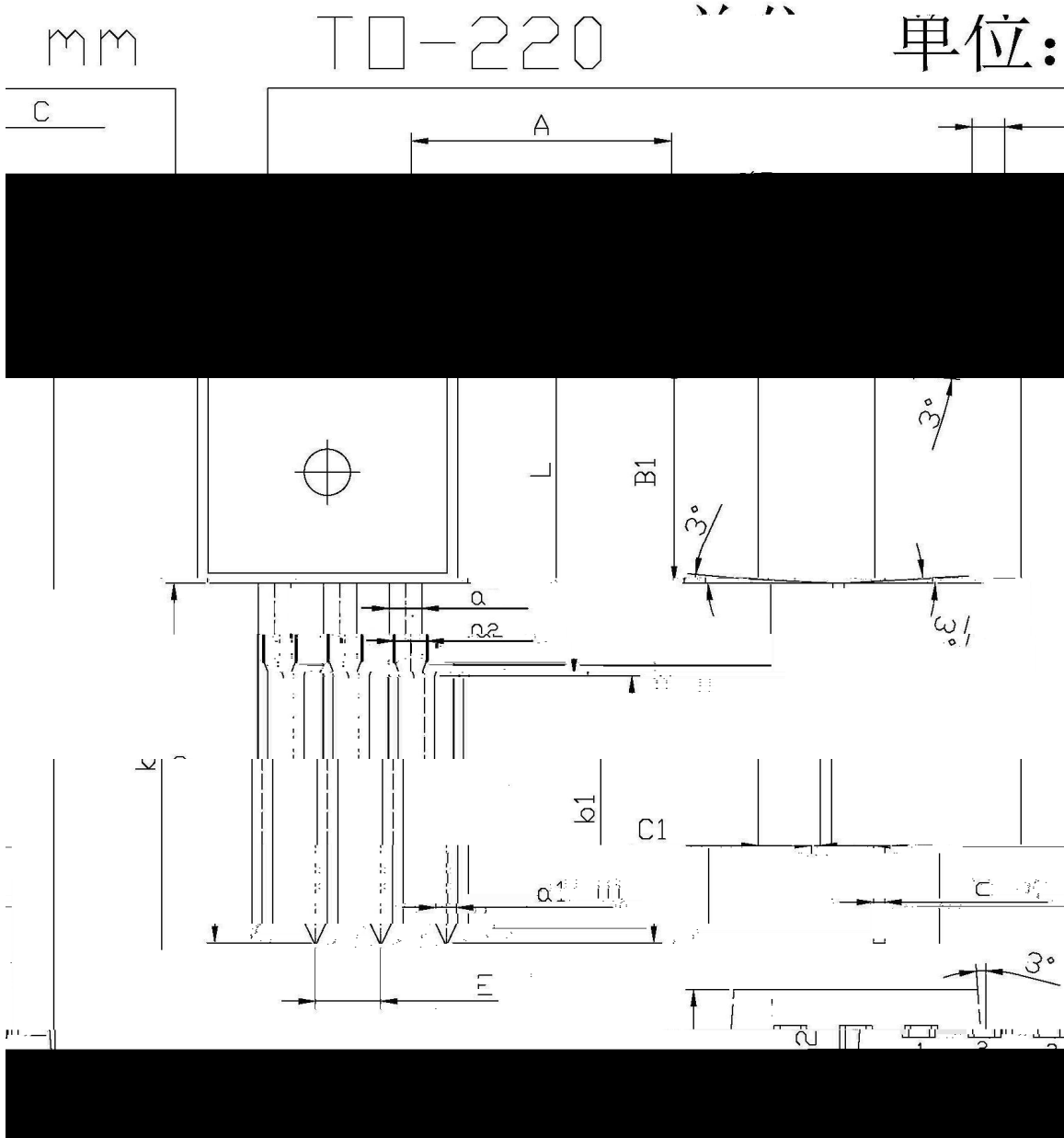
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Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-15	A
Base Current – Continuous	I_B	-5.0	A
Collector Power Dissipation	$P_C(T_C=25 \text{ }^\circ\text{C})$	90	W
Junction Temperature	T_j	150	

/ Electrical Characteristic Curve

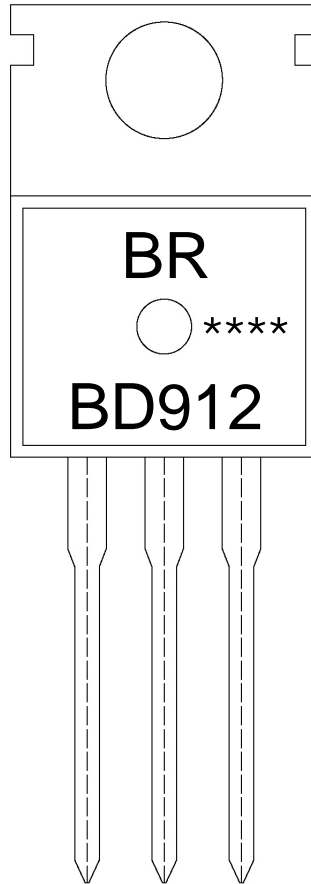


/ Package Dimensions



Symbol	Dimensions in Millimeters		Symbol	Dimensions in Millimeters	
	Min	Max		Min	Max
A	9.8	10.2	C	1.2	1.4
B1	9.0	9.6	C1	15.7	16.1
a	1.22	1.32	k	0.94	1.06
b1	1.25	1.45	L	0.4	0.6

/ Marking Instructions



BR

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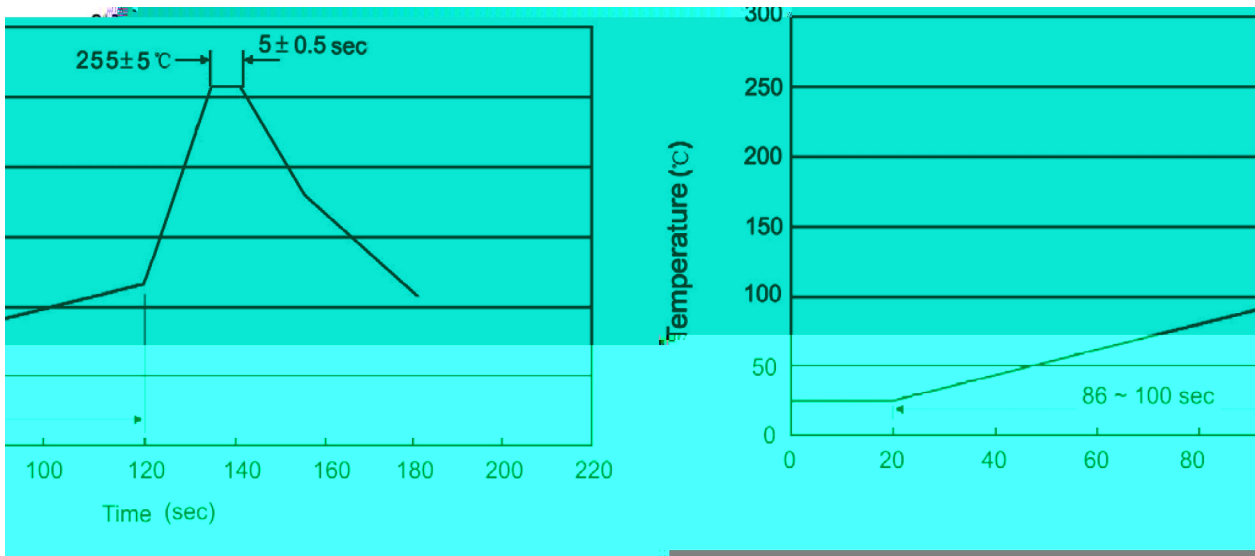
Note:

BR: Company Code

BD912: Product Type.

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-------|-----|-----------|--------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255±5 | | 5±0.5sec; | | 2.Peak Temp.:255±5 , Duration:5±0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270±5 10±1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱
TO-220/F	200	10	2,000	5	10,000	135×190	237×172×102	560×245×195